Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	332	(438/312).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 09:43
S2	91	GaInAsN	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 09:45
S3	45	S2 and (@ad<"20001127" @rlad<"20001127")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 10:08
S4	4114	carbon near3 doped	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 09:49
S5	1	S3 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 09:48
S6	23310	(carbon or p-type) near3 doped	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 09:53
S7	11	S3 and S6	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 09:55
S8	8610	"heterojunction bipolar transistor" hbt	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 09:56

S9	18	S2 and S8	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 10:07
S10	888	S8 and S6	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 10:08
S11	455	S10 and "base layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 10:10
S12	223	S11 and (@ad<"20001127" @rlad<"20001127")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 10:11
S13	720	S10 and (base near2 (layer region))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 10:11
S14	299	S13 and (@ad<"20001127" @rlad<"20001127")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 11:31
S15	299	S14 and dop$3	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 10:24
S16	164176	"metalorganic chemical vapor deposition" mocvd "chemical vapor deposition" cvd	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 11:29
S17	24324	S16 and (ammonia "NH.sub.4" dimethylhydrazine "(CH.sub.3).sub.2NNH.sub.2" "(CH.sub.3).sub.2N.sub.2H.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 11:30

S18	14984	S17 and (@ad<"20001127" @rlad<"20001127")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 12:25
S19	621	S18 and "nitrogen source"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 12:26
S20	13	S18 and (GaInAsN "Ga.sub. 1-xIn.sub.xAs.sub.1-y N.sub. y")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 12:57
S21	91	GaInAsN "Ga.sub.1-xIn.sub. xAs.sub.1-y N.sub.y"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/26 07:57
S22	61	S21 and ratio	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 12:58
S23	53	S22 not welser	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/23 12:58
S24	15	(("20010040244") or ("6031256") or ("5606185") or ("6285044") or ("6150677") or ("20020102847") or ("6150677") or ("20020027232") or ("4518979") or ("5371389") or ("5429957") or ("5571732") or ("5814843") or ("5858818") or ("5903018") or ("6847060")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/23 13:36
S25	389	GaInAsN "Ga.sub.1-xIn.sub. xAs.sub.1-y N.sub.y" InGaAsN	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/26 09:12

S26	223	S25 and ratio	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/26 07:58
S27	215	S26 not welser	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/26 07:59
S28	86	S27 and (@ad<"20001127" @rlad<"20001127")	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/26 08:32
S30	304	"double heterojunction bipolar transistor" dhbt	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/27 07:23
S31	30	S30 and (emitter near (InGaP AlInGaP AlGaAs))	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/26 08:32
S32	23	S31 not welser	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/26 08:32
S33	13	S32 and (@ad<"20001127" @rlad<"20001127")	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/26 09:14
S34	11	S25 and "transitional layer"	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/26 09:15
S38	11	S25 and transitional	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/26 09:15

S39	133	S25 and transition$3	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/26 09:15
S40	52	S39 and (@ad<"20001127" @rlad<"20001127")	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/26 09:15
S41	3382	((257/103,197,198) or (600/615)).CCLS.	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	OFF	2005/09/27 07:24
S42	77	S41 and (GaInAsN InGaAsN GaInNAs InGaNAs)	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/27 07:24
S43	34	S42 and (@ad<"20001127" @rlad<"20001127")	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/27 08:33
S44	32	S43 and dop$3	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/27 08:32
S45	12183	(GaAs InGaAs InGaAsN) same (InGaP AlGaAs)	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/27 08:33
S46	8786	S45 and (@ad<"20001127" @rlad<"20001127")	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/27 08:33
S47	15	S46 and "transitional layer"	US-PGPU B; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/27 08:33